THE DATASHEET OF

TPA6211AIDGNR

TPA6211A1-Q1 3.1-W Mono Fully Differential Audio Power Amplifier

1 Features

- Qualified for automotive applications
  - Device HBM ESD classification level 3A
  - Device CDM ESD classification level C6
- 3.1 W into 3 Ω from a 5-V supply at THD = 10% (typical)
- Low supply current: 4 mA (typical) at 5 V
- Shutdown current: 0.01 µA (typical)
- Fast startup with minimal pop
- Only three external components
  - Improved PSRR (–80 dB) and wide supply voltage (2.5 V to 5.5 V) for direct battery operation
  - Fully differential design reduces RF rectification
  - –63-dB CMRR Eliminates two input coupling capacitors

2 Applications

- Automotive audio
- Emergency calls
- Driver notifications
- Cluster chimes

3 Description

The TPA6211A1-Q1 device is a 3.1-W mono fully-differential amplifier designed to drive a speaker with at least 3-Ω impedance while consuming only 20-mm^2 total printed-circuit board (PCB) area in most applications. The device operates from 2.5 V to 5.5 V, drawing only 4 mA of quiescent supply current. The TPA6211A1-Q1 device is available in the space-saving 8-pin MSOP (DGN) PowerPAD™ package.

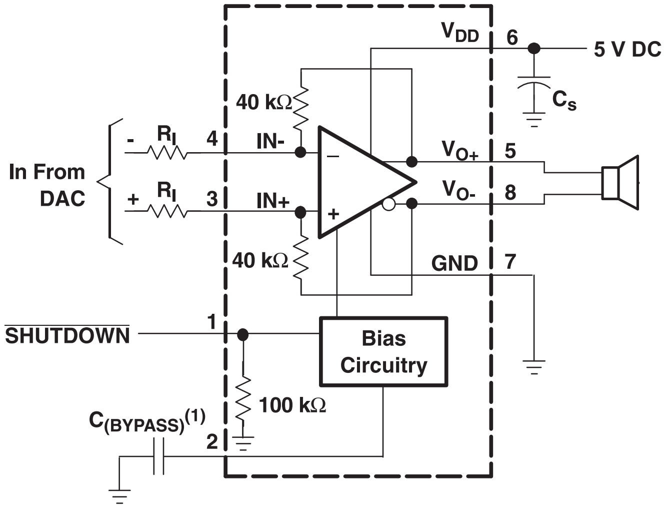
The device includes features such as a –80-dB supply voltage rejection from 20 Hz to 2 kHz, improved RF-rectification immunity, small PCB area, and a fast start-up with minimal pop makes the TPA6211A1-Q1 device ideal for emergency call applications. Additionally, the device supports low-power needs in infotainment and cluster applications, such as cluster chimes or driver notification.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPA6211A1-Q1	MSOP-PowerPAD (8)	3.00 mm × 3.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Application Circuit



(1) C$_{(BYPASS)}$ is optional

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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (August 2016) to Revision D	Page
• Deleted *AEC-Q100* from the Feature: Qualified for automotive applications	1
• Deleted Feature: Temperature Grade 2	1
• Changed the *ESD Ratings* table	3

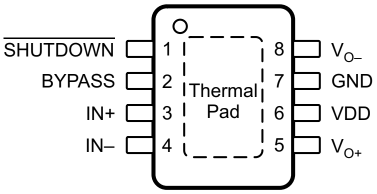
Changes from Revision B (January 2014) to Revision C	Page
• Added *Device Information* table, *ESD Ratings* table, *Feature Description* section, *Device Functional Modes* section, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section.	1
• Added missing Max Ambient Temperature values to Table 2	14
• Changed 45.9 to 71.7, 1.27 to 1.25, and 91.7 to 60 in Equation 12	15

Changes from Revision A (November 2013) to Revision B	Page
• Added three new equations to the *DIFFERENTIAL OUTPUT VERSUS SINGLE-ENDED OUTPUT* section in order to show difference between single-ended and differential output	15

Changes from Original (June 2011) to Revision A	Page
• Deleted *Designed for Wireless or Cellular Handsets and PDAs* from *Features* list.	1
• Deleted *Ordering Information* table	3
• Changed reference from "equation 6" to Equation 25 in the *High-Pass Filter* section.	20

5 Pin Configuration and Functions

DGN Package
8-Pin MSOP-PowerPAD
Top View



Not to scale

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
BYPASS	2	I	Mid-supply voltage, adding a bypass capacitor improves PSRR
GND	7	I	High-current ground
IN–	4	I	Negative differential input
IN+	3	I	Positive differential input
$\overline{\text{SHUTDOWN}}$	1	I	Shutdown pin (active low logic)
Thermal Pad	—	—	Connect to ground. Thermal pad must be soldered down in all applications to properly secure device on the PCB.
V_{DD}	6	I	Power supply
V_{O+}	5	O	Positive BTL output
V_{O-}	8	O	Negative BTL output

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range unless otherwise noted(1)

		MIN	MAX	UNIT
Supply voltage, V_{DD}		–0.3	6	V
Input voltage, V_I		–0.3	V_{DD} + 0.3 V	V
Continuous total power dissipation		See *Dissipation Ratings*		
Lead temperature 1.6 mm (1/16 Inch) from case for 10 s	DGN		260	°C
Operating free-air temperature, T_A		–40	105	°C
Junction temperature, T_J		–40	150	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002(1)	±4000	V
		Charged-device model (CDM), per AEC Q100-011	±1000	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

			MIN	MAX	UNIT
V_{DD}	Supply voltage		2.5	5.5	V
V_{IH}	High-level input voltage	$\overline{\text{SHUTDOWN}}$	1.55		V
V_{IL}	Low-level input voltage	$\overline{\text{SHUTDOWN}}$		0.5	V
T_A	Operating free-air temperature		–40	105	°C

6.4 Thermal Information

THERMAL METRIC[1]		TPA6211A1-Q1	UNIT
		DGN (MSOP-PowerPAD)	
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	71.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	55.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	44.9	°C/W
ψ_{JT}	Junction-to-top characterization parameter	3.7	°C/W
ψ_{JB}	Junction-to-board characterization parameter	44.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	19.6	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

$T_A = 25°C$

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{OS}	Output offset voltage (measured differentially)	V_I = 0-V differential, Gain = 1 V/V, V_{DD} = 5.5 V		–9	0.3	9	mV
PSRR	Power supply rejection ratio	V_{DD} = 2.5 V to 5.5 V			–85	–60	dB
V_{IC}	Common mode input range	V_{DD} = 2.5 V to 5.5 V		0.5		V_{DD} – 0.8	V
CMRR	Common mode rejection ratio	V_{DD} = 5.5 V, V_{IC} = 0.5 V to 4.7 V			–63	–40	dB
		V_{DD} = 2.5 V, V_{IC} = 0.5 V to 1.7 V			–63	–40	
	Low-output swing	R_L = 4 Ω, V_{IN+} = V_{DD}, V_{IN+} = 0 V, Gain = 1 V/V, V_{IN-} = 0 V or V_{IN-} = V_{DD}	V_{DD} = 5.5 V		0.45		V
			V_{DD} = 3.6 V		0.37		
			V_{DD} = 2.5 V		0.26	0.4	
	High-output swing	R_L = 4 Ω, V_{IN+} = V_{DD}, V_{IN-} = V_{DD}, Gain = 1 V/V, V_{IN-} = 0 V or V_{IN+} = 0 V	V_{DD} = 5.5 V		4.95		V
			V_{DD} = 3.6 V		3.18		
			V_{DD} = 2.5 V	2	2.13		
$\lvert I_{IH} \rvert$	High-level input current, shutdown	V_{DD} = 5.5 V, V_I = 5.8 V			58	100	µA
$\lvert I_{IL} \rvert$	Low-level input current, shutdown	V_{DD} = 5.5 V, V_I = –0.3 V			3	100	µA
I_Q	Quiescent current	V_{DD} = 2.5 V to 5.5 V, no load			4	5	mA
$I_{(SD)}$	Supply current	$V_{\overline{SHUTDOWN}}$ ≤ 0.5 V, V_{DD} = 2.5 V to 5.5 V, R_L = 4 Ω			0.01	1	µA
	Gain	R_L = 4 Ω		$\frac{38\ k\Omega}{R_I}$	$\frac{40\ k\Omega}{R_I}$	$\frac{42\ k\Omega}{R_I}$	V/V
	Resistance from shutdown to GND				100		kΩ

6.6 Operating Characteristics

T_A = 25°C, Gain = 1 V/V

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
P_O	Output power	THD + N = 1%, f = 1 kHz, R_L = 3 Ω	V_{DD} = 5 V		2.45		W
			V_{DD} = 3.6 V		1.22		
			V_{DD} = 2.5 V		0.49		
		THD + N = 1%, f = 1 kHz, R_L = 4 Ω	V_{DD} = 5 V		2.22		
			V_{DD} = 3.6 V		1.1		
			V_{DD} = 2.5 V		0.47		
		THD + N = 1%, f = 1 kHz, R_L = 8 Ω	V_{DD} = 5 V		1.36		
			V_{DD} = 3.6 V		0.72		
			V_{DD} = 2.5 V		0.33		
THD+N	Total harmonic distortion plus noise	f = 1 kHz, R_L = 3 Ω	P_O = 2 W, V_{DD} = 5 V		0.045%		
			P_O = 1 W, V_{DD} = 3.6 V		0.05%		
			P_O = 300 mW, V_{DD} = 2.5 V		0.06%		
		f = 1 kHz, R_L = 4 Ω	P_O = 1.8 W, V_{DD} = 5 V		0.03%		
			P_O = 0.7 W, V_{DD} = 3.6 V		0.03%		
			P_O = 300 mW, V_{DD} = 2.5 V		0.04%		
		f = 1 kHz, R_L = 8 Ω	P_O = 1 W, V_{DD} = 5 V		0.02%		
			P_O = 0.5 W, V_{DD} = 3.6 V		0.02%		
			P_O = 200 mW, V_{DD} = 2.5 V		0.03%		
k_{SVR}	Supply ripple rejection ratio	V_{DD} = 3.6 V, Inputs AC-grounded with C_I = 2 μF, V_{RIPPLE} = 200 mV_{pp}	f = 217 Hz		–80		dB
			f = 20 Hz to 20 kHz		–70		
SNR	Signal-to-noise ratio	V_{DD} = 5 V, P_O = 2 W, R_L = 4 Ω			105		dB
V_n	Output voltage noise	V_{DD} = 3.6 V, f = 20 Hz to 20 kHz, Inputs AC-grounded with C_I = 2 μF	No weighting		15		μV_{RMS}
			A weighting		12		
CMRR	Common mode rejection ratio	V_{DD} = 3.6 V, V_{IC} = 1 V_{pp}	f = 217 Hz		–65		dB
Z_I	Input impedance			38	40	44	kΩ
	Start-up time from shutdown	V_{DD} = 3.6 V, No C_{BYPASS}			4		μs
		V_{DD} = 3.6 V, C_{BYPASS} = 0.1 μF			27		ms

6.7 Dissipation Ratings

PACKAGE	$T_A \leq 25°C$ POWER RATING	DERATING FACTOR[1]	T_A = 70°C POWER RATING	T_A = 85°C POWER RATING
DGN	2.13 W	17.1 mW/°C	1.36 W	1.11 W

(1) Derating factor based on High-k board layout.

6.8 Typical Characteristics

Table 1. Table of Graphs

		FIGURE
Output power	vs Supply voltage	Figure 1
	vs Load resistance	Figure 2
Power dissipation	vs Output power	Figure 3, Figure 4
Total harmonic distortion + noise	vs Output power	Figure 5, Figure 6, Figure 7
	vs Frequency	Figure 8, Figure 9, Figure 10, Figure 11, Figure 12
	vs Common-mode input voltage	Figure 13
Supply voltage rejection ratio	vs Frequency	Figure 14, Figure 15, Figure 16, Figure 17
Supply voltage rejection ratio	vs Common-mode input voltage	Figure 18
GSM Power supply rejection	vs Time	Figure 19
GSM Power supply rejection	vs Frequency	Figure 20
Common-mode rejection ratio	vs Frequency	Figure 21
	vs Common-mode input voltage	Figure 22
Closed loop gain/phase	vs Frequency	Figure 23
Open loop gain/phase	vs Frequency	Figure 24
Supply current	vs Supply voltage	Figure 25
	vs Shutdown voltage	Figure 26
Start-up time	vs Bypass capacitor	Figure 27

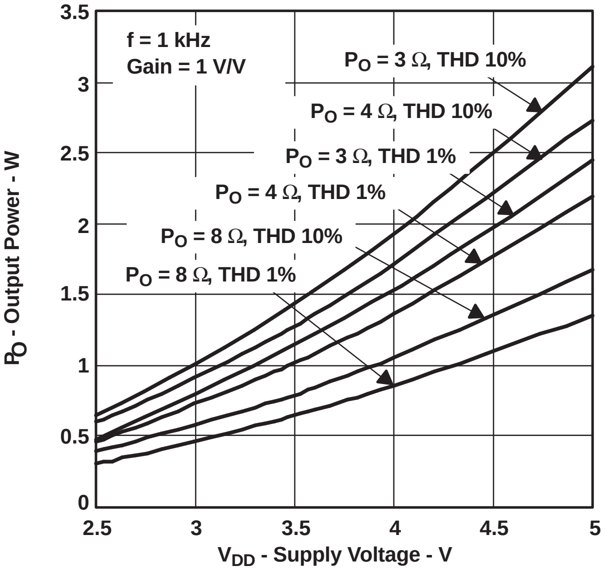


Figure 1. Output Power vs Supply Voltage

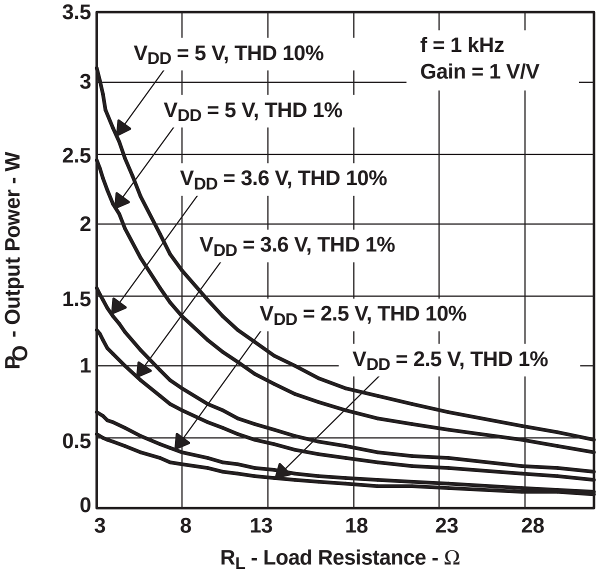


Figure 2. Output Power vs Load Resistance

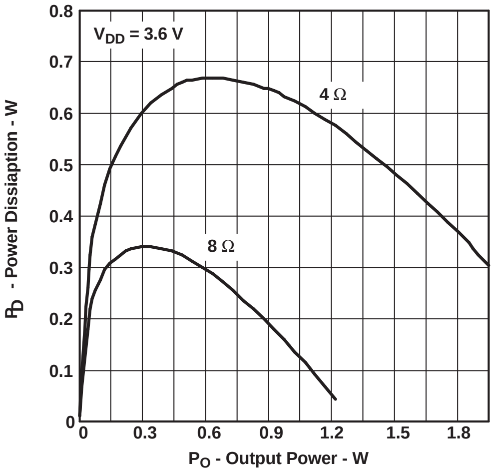


Figure 3. Power Dissipation vs Output Power

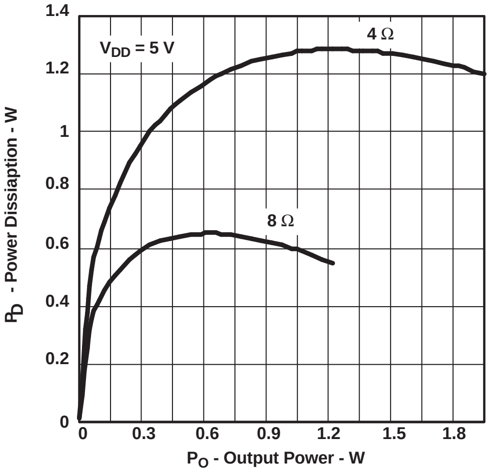


Figure 4. Power Dissipation vs Output Power

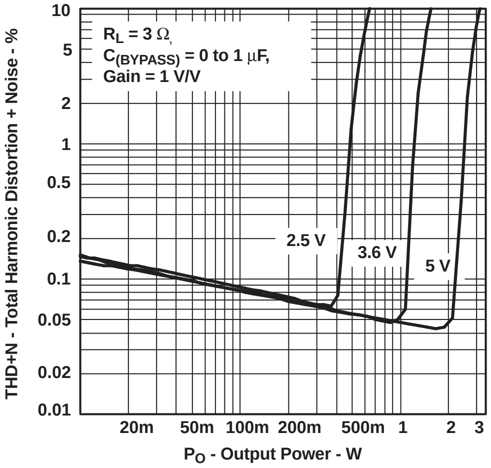


Figure 5. Total Harmonic Distortion + Noise vs Output Power

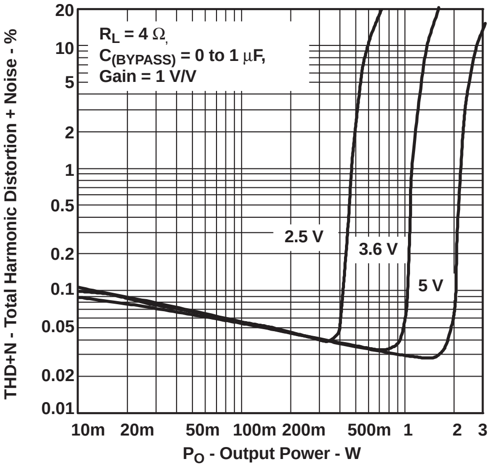


Figure 6. Total Harmonic Distortion + Noise vs Output Power

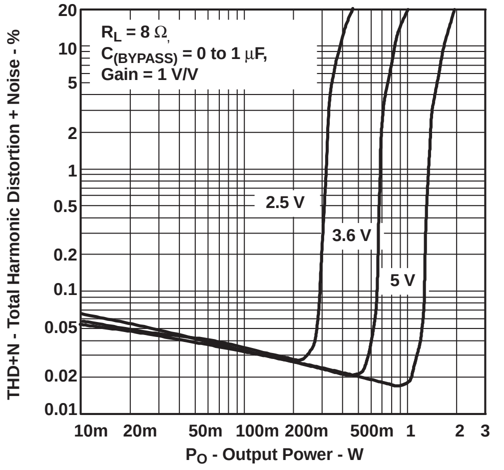


Figure 7. Total Harmonic Distortion + Noise vs Output Power

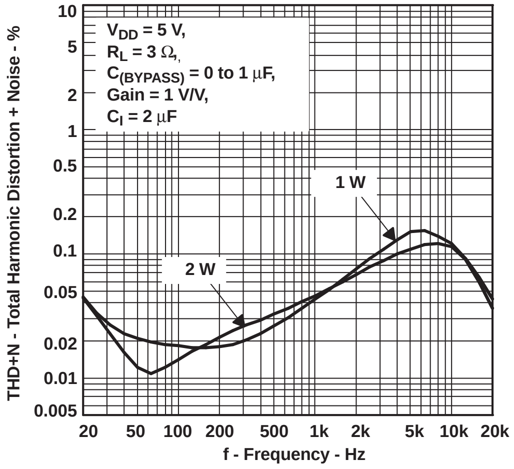


Figure 8. Total Harmonic Distortion + Noise vs Frequency

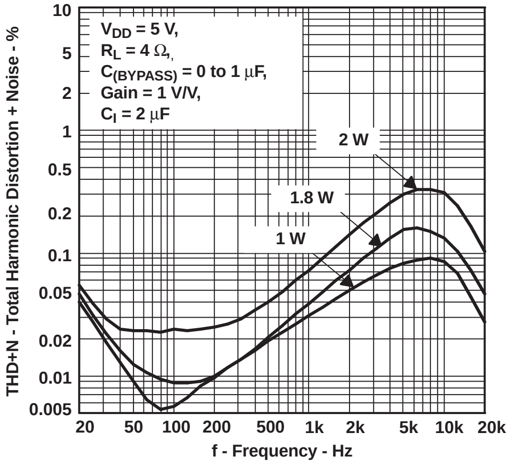


Figure 9. Total Harmonic Distortion + Noise vs Frequency

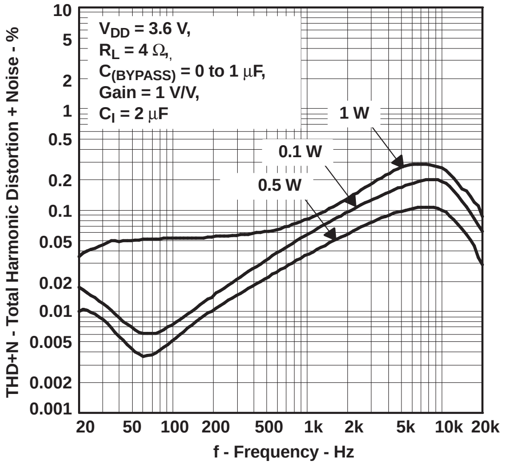


Figure 10. Total Harmonic Distortion + Noise vs Frequency

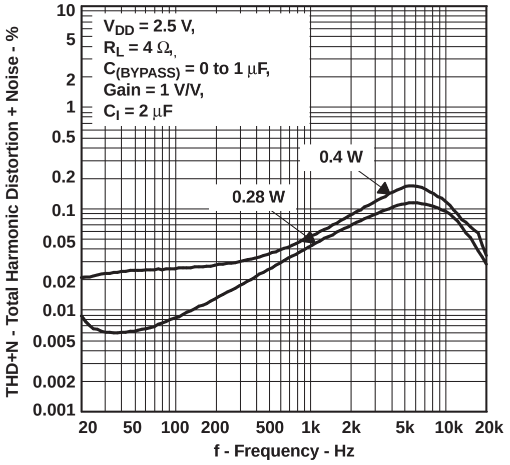


Figure 11. Total Harmonic Distortion + Noise vs Frequency

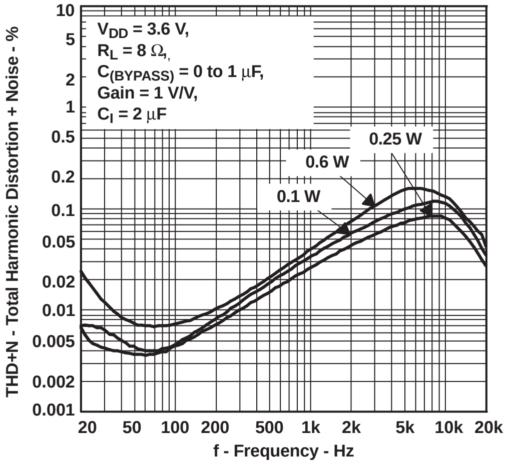


Figure 12. Total Harmonic Distortion + Noise vs Frequency

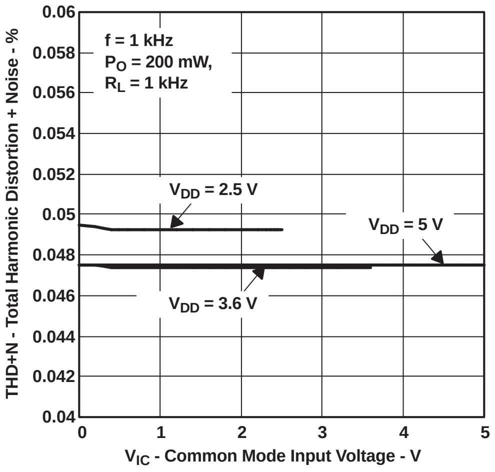


Figure 13. Total Harmonic Distortion + Noise vs Common-Mode Input Voltage

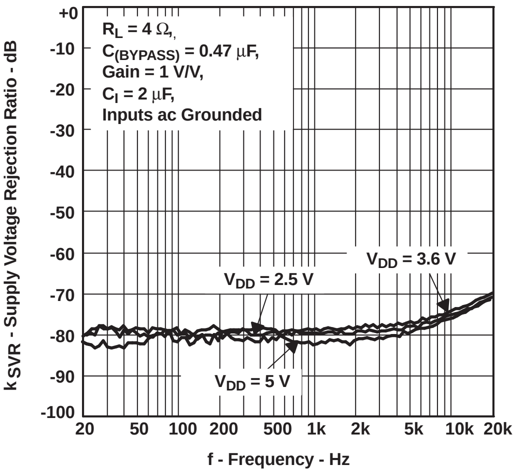


Figure 14. Supply Voltage Rejection Ratio vs Frequency

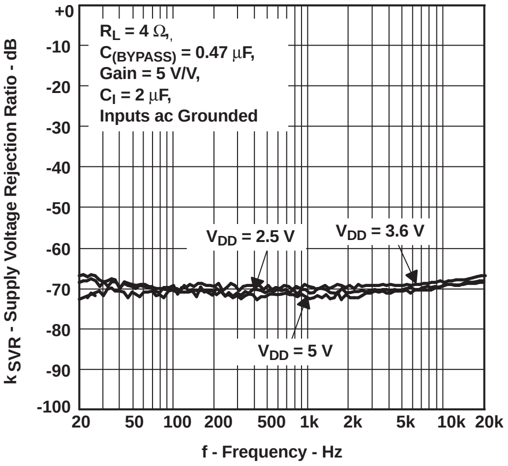


Figure 15. Supply Voltage Rejection Ratio vs Frequency

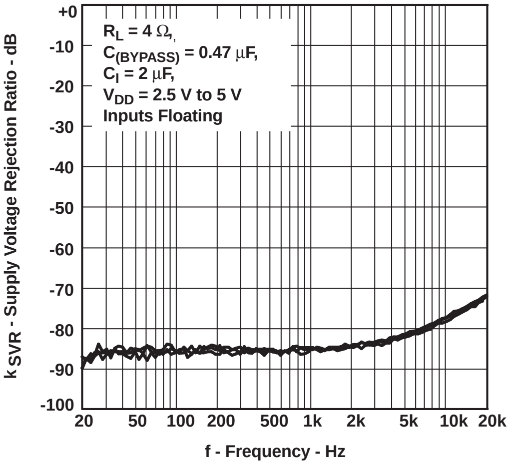


Figure 16. Supply Ripple Rejection Ratio vs Frequency

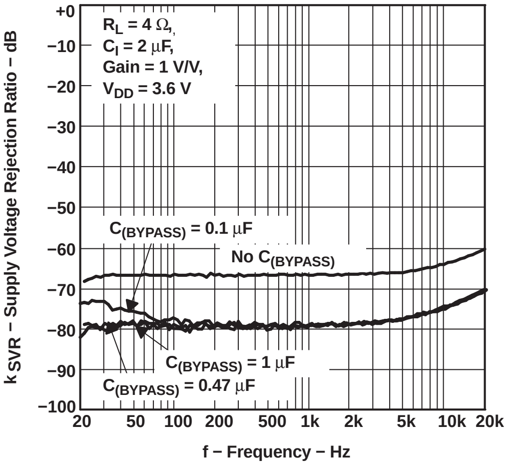


Figure 17. Supply Voltage Rejection Ratio vs Frequency

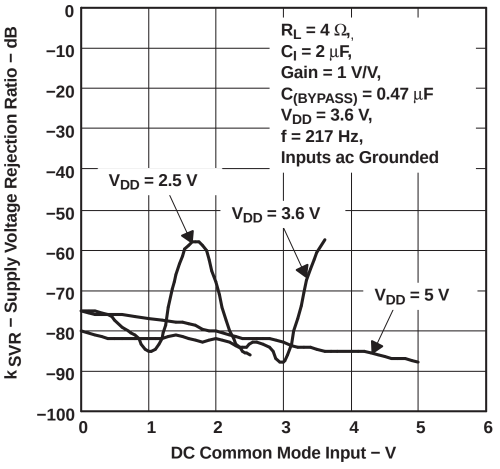


Figure 18. Supply Voltage Rejection Ratio vs DC Common-Mode Input

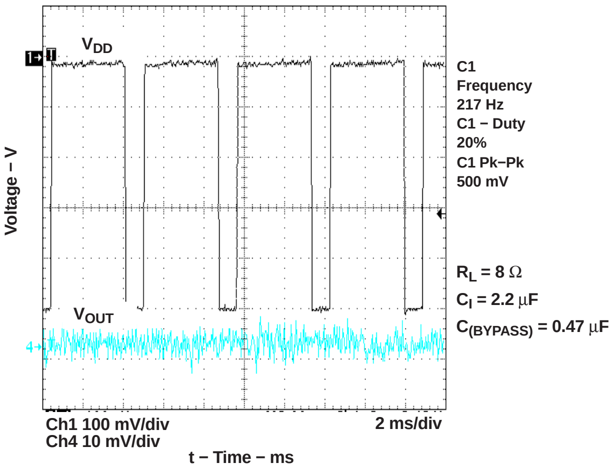


Figure 19. GSM Power Supply Rejection vs Time

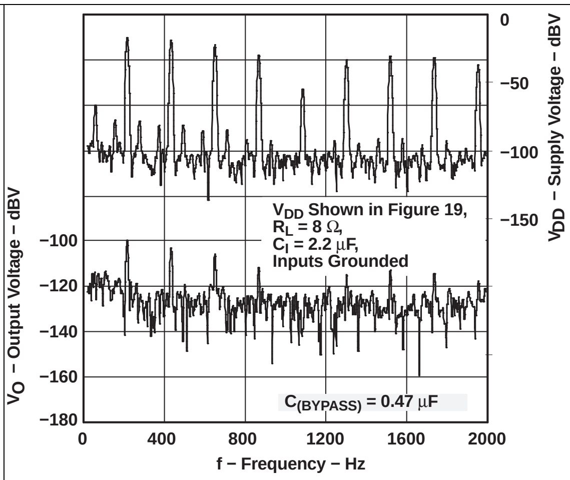


Figure 20. GSM Power Supply Rejection vs Frequency

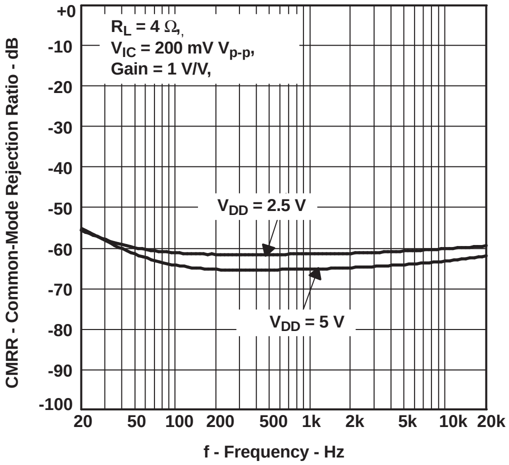


Figure 21. Common-Mode Rejection Ratio vs Frequency

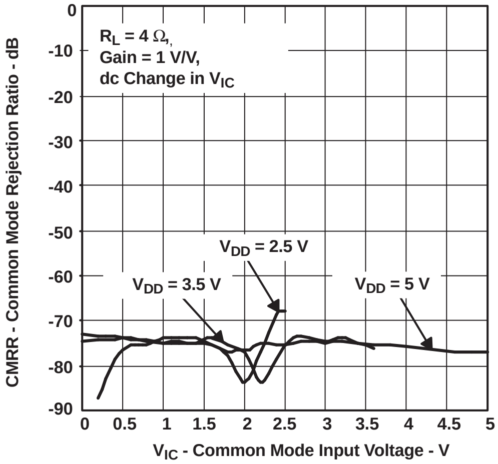


Figure 22. Common-Mode Rejection Ratio vs Common-Mode Input Voltage

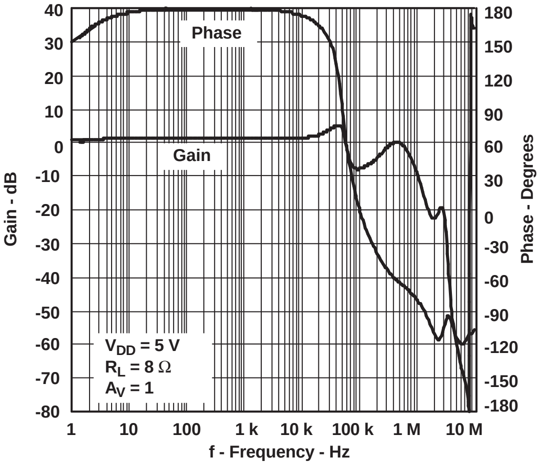


Figure 23. Closed Loop Gain/Phase vs Frequency

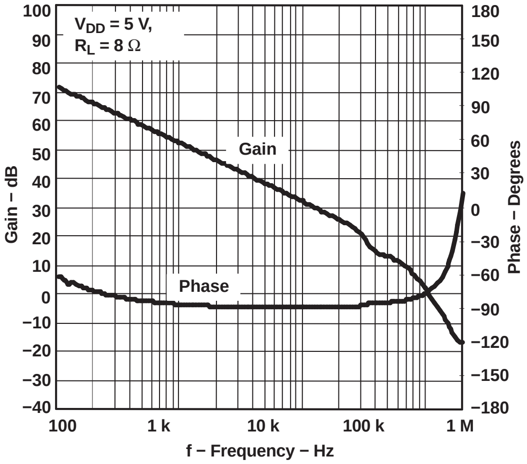


Figure 24. Open Loop Gain/Phase vs Frequency

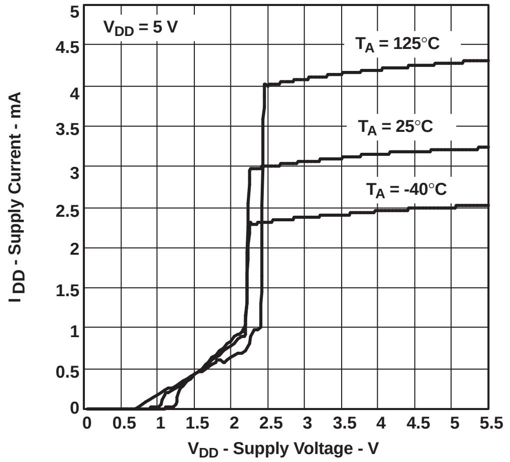


Figure 25. Supply Current vs Supply Voltage

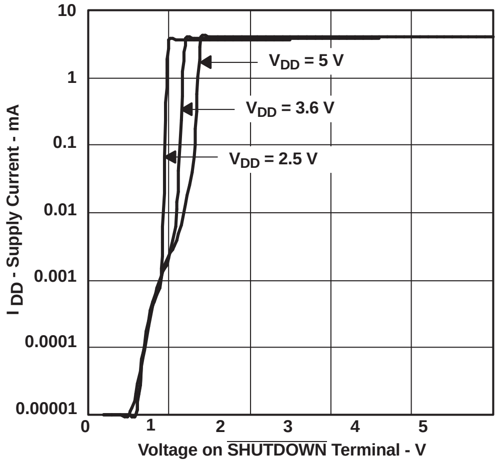


Figure 26. Supply Current vs Shutdown Voltage

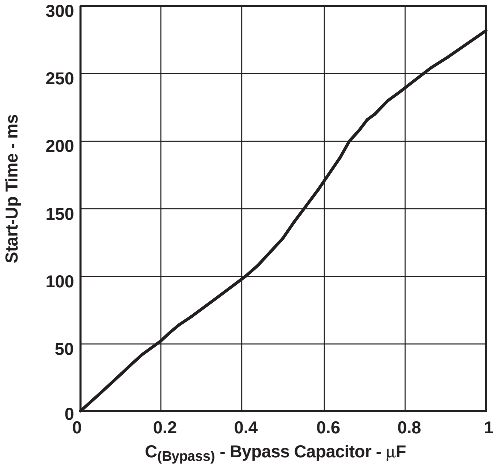


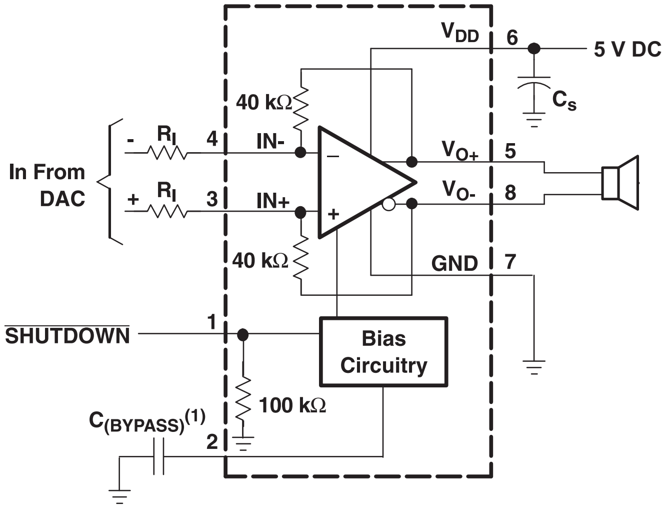
Figure 27. Start-up Time vs Bypass Capacitor

7 Detailed Description

7.1 Overview

The TPA6211A1-Q1 device is a fully differential amplifier with differential inputs and outputs. The fully differential amplifier consists of a differential amplifier and a common-mode amplifier. The differential amplifier ensures that the amplifier outputs a differential voltage that is equal to the differential input times the gain. The common-mode feedback ensures that the common-mode voltage at the output is biased around V_{DD} / 2 regardless of the common-mode voltage at the input.

7.2 Functional Block Diagram



(1) $C_{(BYPASS)}$ is optional

7.3 Feature Description

7.3.1 Advantages of Fully Differential Amplifiers

Input coupling capacitors are not required. A fully differential amplifier with good CMRR, such as the TPA6211A1-Q1 device, allows the inputs to be biased at voltage other than mid-supply. For example, if a DAC has a lower mid-supply voltage than that of the TPA6211A1-Q1 device, the common-mode feedback circuit compensates, and the outputs are still biased at the mid-supply point of the TPA6211A1-Q1 device. The inputs of the TPA6211A1-Q1 device can be biased from 0.5 V to V_{DD} – 0.8 V. If the inputs are biased outside of that range, input coupling capacitors are required.

A Mid-supply bypass capacitor, C_{BYPASS}, is not required. The fully differential amplifier does not require a bypass capacitor. Any shift in the mid-supply voltage affects both positive and negative channels equally, thus canceling at the differential output. Removing the bypass capacitor slightly worsens power supply rejection ratio (k_{SVR}), but a slight decrease of k_{SVR} can be acceptable when an additional component can be eliminated (see Figure 17).

The RF-immunity is improved. A fully differential amplifier cancels the noise from RF disturbances much better than the typical audio amplifier.

7.3.2 Fully Differential Amplifier Efficiency and Thermal Information

Class-AB amplifiers are inefficient, primarily because of voltage drop across the output-stage transistors. The two components of this internal voltage drop are the headroom or DC voltage drop that varies inversely to output power, and the sinewave nature of the output. The total voltage drop can be calculated by subtracting the RMS value of the output voltage from V_{DD}. The internal voltage drop multiplied by the average value of the supply current, I_{DD}(avg), determines the internal power dissipation of the amplifier.

An easy-to-use equation to calculate efficiency starts out as being equal to the ratio of power from the power supply to the power delivered to the load. To accurately calculate the RMS and average values of power in the load and in the amplifier, the current and voltage waveform shapes must first be understood (see Figure 28).

Feature Description (continued)

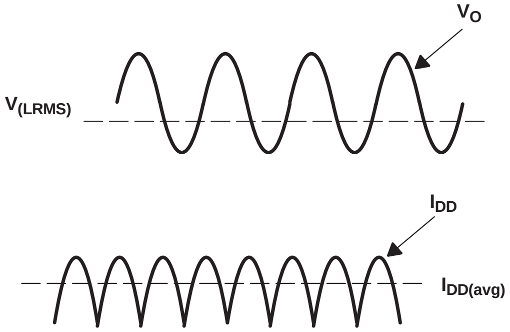


Figure 28. Voltage and Current Waveforms for BTL Amplifiers

Although the voltages and currents for SE and BTL are sinusoidal in the load, currents from the supply are different between SE and BTL configurations. In an SE application the current waveform is a half-wave rectified shape, whereas in BTL the current waveform is a full-wave rectified waveform. This means RMS conversion factors are different. Keep in mind that for most of the waveform both the push and pull transistors are not on at the same time, which supports the fact that each amplifier in the BTL device only draws current from the supply for half the waveform. Equation 1 to Equation 10 are the basis for calculating amplifier efficiency.

$$\eta_{BTL} = \frac{P_L}{P_{SUP}}$$

where

- η_{BTL} is the efficiency of a BTL amplifier
- P_L is the power delivered to load
- P_{SUP} is the power drawn from power supply (1)

P_L is calculated with Equation 2, and V_{LRMS} is calculated with Equation 3.

$$P_L = \frac{{V_{LRMS}}^2}{R_L}$$

where

- V_{LRMS} = RMS voltage on BTL load
- R_L is load resistance (2)

$$V_{LRMS} = \frac{V_P}{\sqrt{2}}$$

where

- V_P is peak voltage on BTL load (3)

Therefore, P_L can be given as Equation 4.

$$P_L = \frac{{V_P}^2}{2 \times R_L} \quad (4)$$

P_{SUP} is calculated with Equation 5.

$P_{SUP} = V_{DD} \times I_{DD}avg$

where

- V_{DD} is power supply voltge
- $I_{DD}avg$ is average current drawn from the power supply (5)

$I_{DD}avg$ is calculated with Equation 6.

Feature Description (continued)

$$I_{DD}avg = \frac{1}{\pi}\int_0^{\pi} \frac{V_P}{R_L} \times \sin(t) \times dt = -\frac{1}{\pi} \times \frac{V_P}{R_L} \times \cos(t)_0^{\pi} = \frac{2 \times V_P}{\pi \times R_L} \tag{6}$$

Therefore, P_{SUP} can be given as Equation 7.

$$P_{SUP} = \frac{2 \times V_{DD} \times V_P}{\pi \times R_L} \tag{7}$$

Substituting for P_L and P_{SUP}, Equation 1 becomes Equation 8

$$\eta_{BTL} = \frac{\frac{V_P{}^2}{2 \times R_L}}{\frac{2 \times V_{DD} \times V_P}{\pi \times R_L}} = \frac{\pi \times V_P}{4 \times V_{DD}} \tag{8}$$

V_P is calculated with Equation 9.

$$V_P = \sqrt{2 \times P_L \times R_L} \tag{9}$$

And substituting for V_P, η_{BTL} can be calculated with Equation 10

$$\eta_{BTL} = \frac{\pi\sqrt{2 \times P_L \times R_L}}{4 \times V_{DD}} \tag{10}$$

A simple formula for calculating the maximum power dissipated (P_{Dmax}) can be used for a differential output application:

$$P_{Dmax} = \frac{2V_{DD}^2}{\pi^2 R_L} \tag{11}$$

Table 2. Efficiency and Maximum Ambient Temperature vs Output Power

OUTPUT POWER	EFFICIENCY	INTERNAL DISSIPATION	POWER FROM SUPPLY	MAX AMBIENT TEMPERATURE
5-V, 3-Ω SYSTEMS				
0.5 W	27.2%	1.34 W	1.84 W	54°C
1 W	38.4%	1.6 W	2.6 W	35°C
2.45 W	60.2%	1.62 W	4.07 W	34°C
3.1 W	67.7%	1.48 W	4.58 W	44°C
5-V, 4-Ω BTL SYSTEMS				
0.5 W	31.4%	1.09 W	1.59 W	72°C
1 W	44.4%	1.25 W	2.25 W	60°C
2 W	62.8%	1.18 W	3.18 W	65°C
2.8 W	74.3%	0.97 W	3.77 W	80°C
5-V, 8-Ω SYSTEMS				
0.5 W	44.4%	0.625 W	1.13 W	105°C (limited by maximum ambient temperature specification)
1 W	62.8%	0.592 W	1.6 W	105°C (limited by maximum ambient temperature specification)
1.36 W	73.3%	0.496 W	1.86 W	105°C (limited by maximum ambient temperature specification)
1.7 W	81.9%	0.375 W	2.08 W	105°C (limited by maximum ambient temperature specification)

Equation 10 is used to calculate efficiencies for four different output power levels, see Table 2. The efficiency of the amplifier is quite low for lower power levels and rises sharply as power to the load is increased resulting in a nearly flat internal power dissipation over the normal operating range. The internal dissipation at full output power is less than in the half power range. Calculating the efficiency for a specific system is the key to proper power supply design. For a 2.8-W audio system with 4-Ω loads and a 5-V supply, the maximum draw on the power supply is almost 3.8 W.

A final point to remember about Class-AB amplifiers is how to manipulate the terms in the efficiency equation to the utmost advantage when possible. In Equation 10, V_{DD} is in the denominator. This indicates that as V_{DD} goes down, efficiency goes up.

The maximum ambient temperature depends on the heat sinking ability of the PCB system. Given $R_{\theta JA}$ (junction-to-ambient thermal resistance), the maximum allowable junction temperature, and the internal dissipation at 1-W output power with a 4-Ohm load, the maximum ambient temperature can be calculated with Equation 12. The maximum recommended junction temperature for the TPA6211A1-Q1 device is 150°C.

$$T_A(\text{Max}) = T_J(\text{Max}) - R_{\theta JA} \times P_D = 150 - 71.7 \times 1.25 = 60°\text{C} \tag{12}$$

Equation 12 shows that the maximum ambient temperature is 60°C at 1-W output power and 4-Ohm load with a 5-V supply.

Table 2 shows that the thermal performance must be considered when using a Class-AB amplifier to keep junction temperatures in the specified range. The TPA6211A1-Q1 device is designed with thermal protection that turns the device off when the junction temperature surpasses 150°C to prevent damage to the IC. In addition, using speakers with an impedance higher than 4 Ω dramatically increases the thermal performance by reducing the output current.

7.3.3 Differential Output Versus Single-Ended Output

Figure 29 shows a Class-AB audio power amplifier (APA) in a fully differential configuration. The TPA6211A1-Q1 amplifier has differential outputs driving both ends of the load. One of several potential benefits to this configuration is power to the load. The differential drive to the speaker means that as one side is slewing up, the other side is slewing down, and vice versa. This in effect doubles the voltage swing on the load as compared to a ground-referenced load. Plugging 2 × $V_{O(PP)}$ into the power equation (Equation 13) yields four-times the output power (as the voltage is squared) from the same supply rail and load impedance (see Equation 15 and Equation 16).

$$V_{(rms)} = \frac{V_{O(PP)}}{2\sqrt{2}}$$

$$\text{Power} = \frac{{V_{(rms)}}^2}{R_L} \tag{13}$$

$$\text{Power}_{(S-E)} = \frac{{V_{(rms)}}^2}{R_L} = \frac{\left(\dfrac{V_{O(PP)}}{2\sqrt{2}}\right)^2}{R_L} = \frac{{V_{O(PP)}}^2}{8R_L} \tag{14}$$

$$\text{Power}_{(Diff)} = \frac{{V_{(rms)}}^2}{R_L} = \frac{\left(\dfrac{2 \times V_{O(PP)}}{2\sqrt{2}}\right)^2}{R_L} = \frac{{V_{O(PP)}}^2}{2R_L} \tag{15}$$

$$\text{Power}_{(Diff)} = 4 \times \text{Power}_{(S-E)} \tag{16}$$

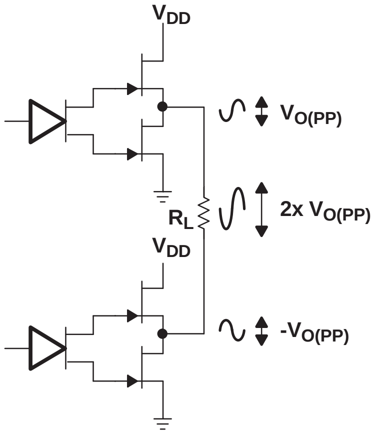


Figure 29. Differential Output Configuration

In a typical automotive application operating at 5 V, bridging raises the power into an 8-Ω speaker from a singled-ended (SE, ground reference) limit of 390 mW to 1.56 W. This is a 6-dB improvement in sound power, or loudness of the sound. In addition to increased power, there are frequency-response concerns. Consider the single-supply SE configuration shown in Figure 30. A coupling capacitor (C_C) is required to block the DC-offset voltage from the load. This capacitor can be quite large (approximately 33 µF to 1000 µF) so it tends to be expensive, heavy, occupy valuable PCB area, and have the additional drawback of limiting low-frequency performance. This frequency-limiting effect is due to the high-pass filter network created with the speaker impedance and the coupling capacitance. This is calculated with Equation 17.

$$f_c = \frac{1}{2\pi R_L C_C} \tag{17}$$

For example, a 68-µF capacitor with an 8-Ω speaker would attenuate low frequencies below 293 Hz. The BTL configuration cancels the DC offsets, which eliminates the need for the blocking capacitors. Low-frequency performance is then limited only by the input network and speaker response. Cost and PCB space are also minimized by eliminating the bulky coupling capacitor.

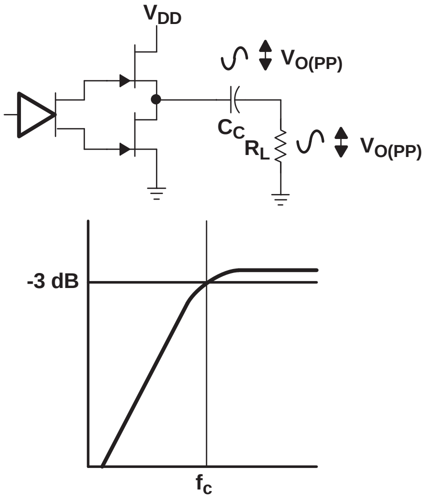


Figure 30. Single-Ended Output and Frequency Response

Increasing power to the load does carry a penalty of increased internal power dissipation. The increased dissipation is understandable considering that the BTL configuration produces four-times the output power of the SE configuration.

7.4 Device Functional Modes

The TPA6211A1-Q1 device can be put in shutdown mode when asserting $\overline{\text{SHUTDOWN}}$ pin to a logic LOW. While in shutdown mode, the device output stage is turned off and set into high impedance, making the current consumption very low. The device exits shutdown mode when a HIGH logic level is applied to $\overline{\text{SHUTDOWN}}$ pin.

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

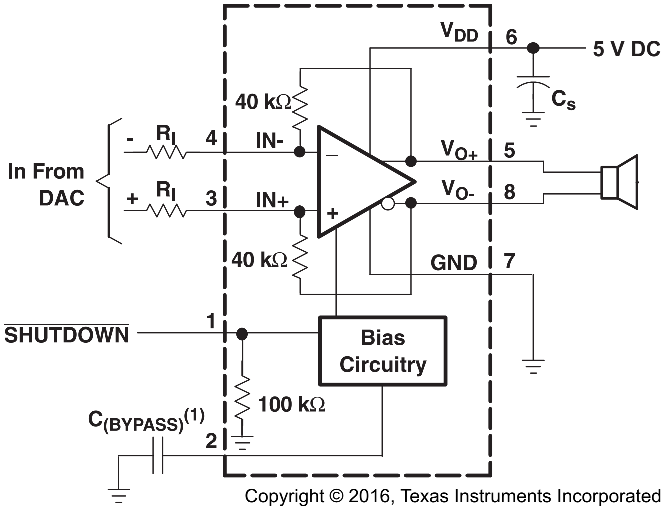
8.1 Application Information

The TPA6211A1-Q1 is a fully-differential amplifier designed to drive a speaker with at least 3-Ω impedance while consuming only 20-mm^2 total printed-circuit board (PCB) area in most applications.

8.2 Typical Applications

Figure 31 shows a typical application circuit for the TPA6211A1-Q1 with a speaker, input resistors, and supporting power supply decoupling capacitors.

8.2.1 Typical Differential Input Application



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(1) $C_{(BYPASS)}$ is optional

Figure 31. Typical Differential Input Application Schematic

Typical values are shown in Table 3.

Table 3. Typical Component Values

COMPONENT	VALUE
R_I	40 kΩ
C_{BYPASS} (1)	0.22 µF
C_S	1 µF
C_I	0.22 µF

(1) C_{BYPASS} is optional.

8.2.1.1 Design Requirements

For this design example, use the parameters listed in Table 4 as the input parameters.

Table 4. Design Parameters

PARAMETER	EXAMPLE VALUE
Power supply voltage	2.5 V to 5.5 V
Current	4 mA to 5 mA
Shutdown	High > 1.55 V
	Low < 0.5 V
Speaker	3 Ω, 4 Ω, or 8 Ω

8.2.1.2 Detailed Design Procedure

8.2.1.2.1 Resistors (R_I)

The input resistor (R_I) can be selected to set the gain of the amplifier according to Equation 18.

$$\text{Gain} = \frac{R_F}{R_I} \tag{18}$$

The internal feedback resistors (R_F) are trimmed to 40 kΩ.

Resistor matching is very important in fully differential amplifiers. The balance of the output on the reference voltage depends on matched ratios of the resistors. CMRR, PSRR, and the cancellation of the second harmonic distortion diminishes if resistor mismatch occurs. Therefore, TI recommends 1%-tolerance resistors or better to optimize performance.

8.2.1.2.2 Bypass Capacitor (C_{BYPASS}) and Start-Up Time

The internal voltage divider at the BYPASS pin of this device sets a mid-supply voltage for internal references and sets the output common mode voltage to V_{DD} / 2. Adding a capacitor filters any noise into this pin, increasing k_{SVR}. C_{BYPASS} also determines the rise time of V_{O+} and V_{O-} when the device exits shutdown. The larger the capacitor, the slower the rise time.

8.2.1.2.3 Input Capacitor (C_I)

The TPA6211A1-Q1 device does not require input coupling capacitors when driven by a differential input source biased from 0.5 V to V_{DD} – 0.8 V. Use 1% tolerance or better gain-setting resistors if not using input coupling capacitors.

In the single-ended input application, an input capacitor (C_I) is required to allow the amplifier to bias the input signal to the proper DC level. In this case, C_I and R_I form a high-pass filter with the corner frequency defined in Equation 19.

$$f_c = \frac{1}{2\pi R_I C_I} \tag{19}$$

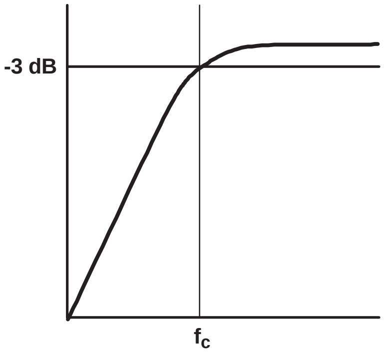


Figure 32. Input Filter Cutoff Frequency

The value of C_I is an important consideration, as it directly affects the bass (low frequency) performance of the circuit. Consider the example where R_I is 10 kΩ and the specification calls for a flat bass response down to 100 Hz. Equation 19 is reconfigured as Equation 20.

$$C_I = \frac{1}{2\pi R_I f_c} \tag{20}$$

In this example, C_I is 0.16 µF, so the likely choice ranges from 0.22 µF to 0.47 µF. TI recommends the use of ceramic capacitors because they are the best choice in preventing leakage current. When polarized capacitors are used, the positive side of the capacitor faces the amplifier input in most applications. The input DC level is held at V_{DD} / 2, typically higher than the source DC level. Confirming the capacitor polarity in the application is important.

8.2.1.2.4 Band-Pass Filter (R_I, C_I, and C_F)

Having signal filtering beyond the one-pole high-pass filter formed by the combination of C_I and R_I can be desirable. A low-pass filter can be added by placing a capacitor (C_F) between the inputs and outputs, forming a band-pass filter.

An example of when this technique might be used would be in an application where the desirable pass-band range is between 100 Hz and 10 kHz, with a gain of 4 V/V. Equation 21 to Equation 28 allow the proper values of C_F and C_I to be determined.

8.2.1.2.4.1 Step 1: Low-Pass Filter

$$f_{c(LPF)} = \frac{1}{2\pi R_F C_F} \tag{21}$$

$$f_{c(LPF)} = \frac{1}{2\pi\, 40\,k\Omega\, C_F} \tag{22}$$

Therefore,

$$C_F = \frac{1}{2\pi 40\ k\Omega\ f_{c(LPF)}} \tag{23}$$

Substituting 10 kHz for $f_{c(LPF)}$ and solving for C_F:

$$C_F = 398\ pF \tag{24}$$

8.2.1.2.4.2 Step 2: High-Pass Filter

$$f_{c(HPF)} = \frac{1}{2\pi R_I C_I} \tag{25}$$

Because the application in this case requires a gain of 4 V/V, R_I must be set to 10 kΩ.

Substituting R_I into Equation 25.

$$f_{c(HPF)} = \frac{1}{2\pi 10\ k\Omega\ C_I} \tag{26}$$

Therefore,

$$C_I = \frac{1}{2\pi 10\ k\Omega\ f_{c(HPF)}} \tag{27}$$

Substituting 100 Hz for $f_{c(HPF)}$ and solving for C_I:

$$C_I = 0.16\ \mu F \tag{28}$$

At this point, a first-order band-pass filter has been created with the low-frequency cutoff set to 100 Hz and the high-frequency cutoff set to 10 kHz.

The process can be taken a step further by creating a second-order high-pass filter. This is accomplished by placing a resistor (R_a) and capacitor (C_a) in the input path. R_a must be at least 10 times smaller than R_I; otherwise its value has a noticeable effect on the gain, as R_a and R_I are in series.

8.2.1.2.4.3 Step 3: Additional Low-Pass Filter

R_a must be at least ten-times smaller than R_I. Set R_a = 1 kΩ

$$f_{c(LPF)} = \frac{1}{2\pi R_a C_a} \tag{29}$$

Therefore,

$$C_a = \frac{1}{2\pi\ 1k\Omega\ f_{c(LPF)}} \tag{30}$$

Substituting 10 kHz for $f_{c(LPF)}$ and solving for C_a:

$$C_a = 160\text{ pF} \tag{31}$$

Figure 33 is a bode plot for the band-pass filter in the previous example. Figure 38 shows how to configure the TPA6211A1-Q1 device as a band-pass filter.

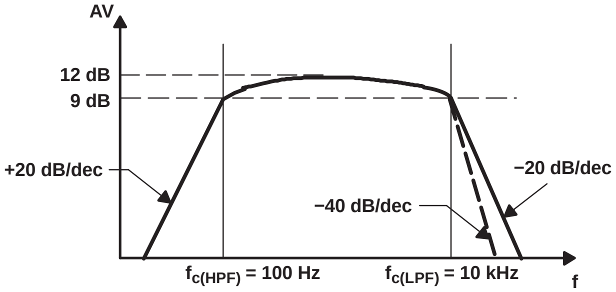


Figure 33. Bode Plot

8.2.1.2.5 Decoupling Capacitor (C_S)

The TPA6211A1-Q1 device is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure the output total harmonic distortion (THD) is as low as possible. Power-supply decoupling also prevents oscillations for long lead lengths between the amplifier and the speaker. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1 µF to 1 µF, placed as close as possible to the device V_{DD} lead works best. For filtering lower frequency noise signals, a 10-µF or greater capacitor placed near the audio power amplifier also helps, but is not required in most applications because of the high PSRR of this device.

8.2.1.2.6 Using Low-ESR Capacitors

Low-ESR capacitors are recommended throughout this applications section. A real (as opposed to ideal) capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance the more the real capacitor behaves like an ideal capacitor.

8.2.1.3 *Application Curves*

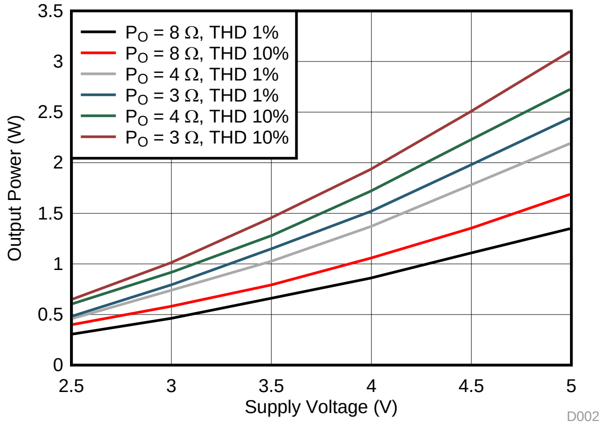


Figure 34. Output Power vs Supply Voltage

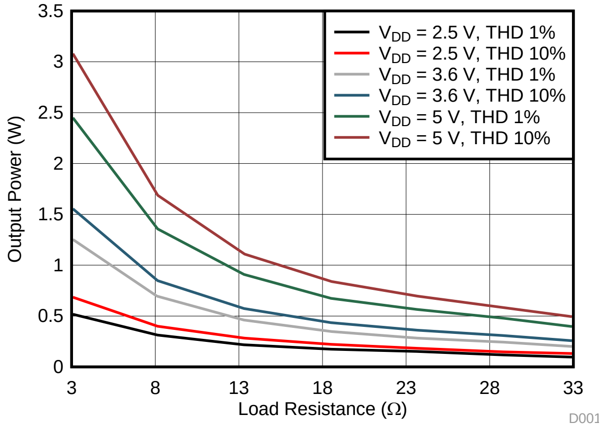
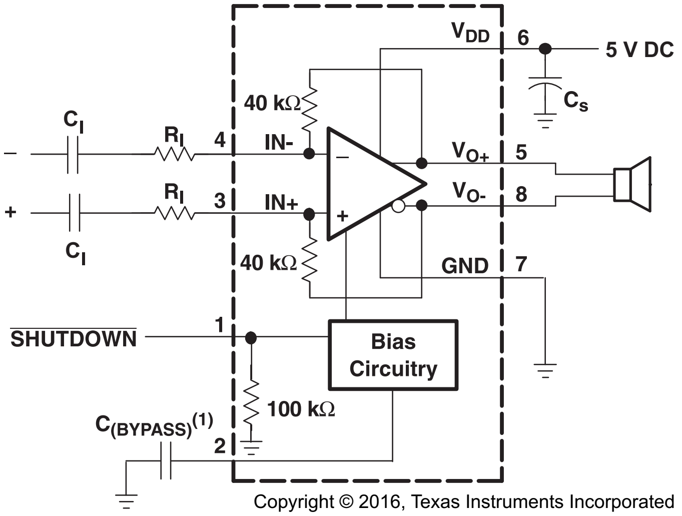


Figure 35. Output Power vs Load Resistance

8.2.2 Other Application Circuits

Figure 36, Figure 37, and Figure 38 show example circuits using the TPA6211A1-Q1 device.



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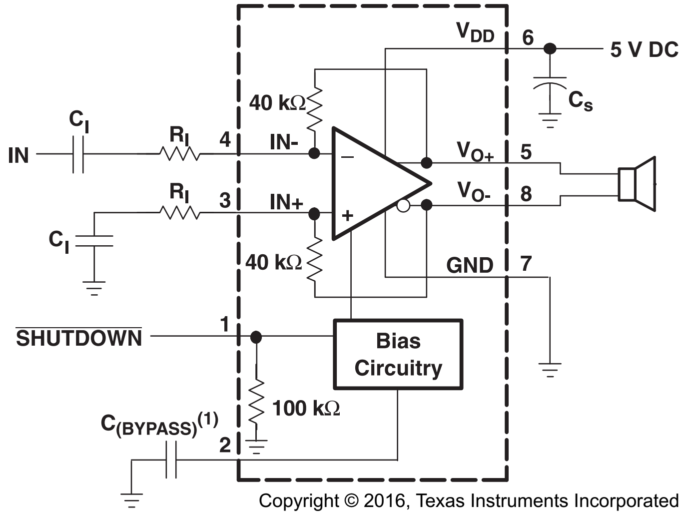
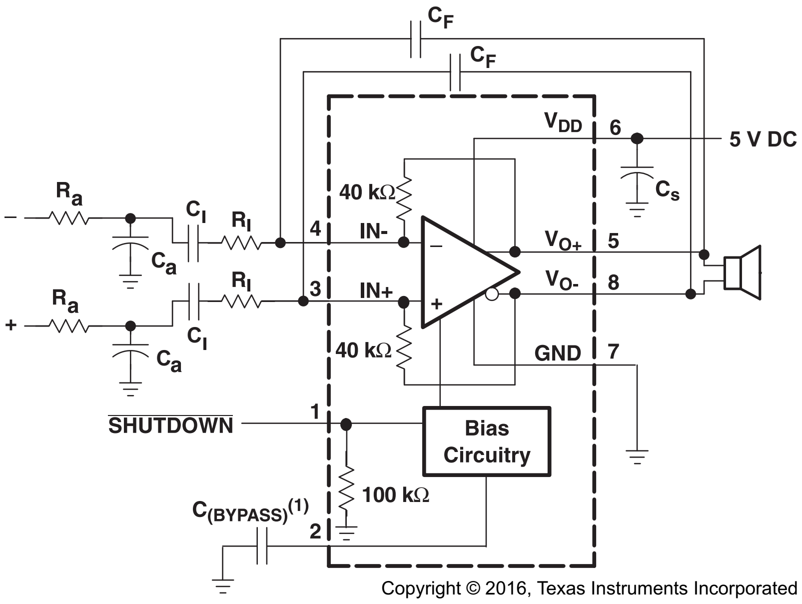
(1) $C_{(BYPASS)}$ is optional

Figure 36. Differential Input Application Schematic Optimized With Input Capacitors



(1) $C_{(BYPASS)}$ is optional

Figure 37. Single-Ended Input Application Schematic



(1) $C_{(BYPASS)}$ is optional

Figure 38. Differential Input Application Schematic With Input Bandpass Filter

9 Power Supply Recommendations

The TPA6211A1-Q1 device is designed to operate from an input voltage supply range between 2.5 V and 5.5 V. Therefore, the output voltage range of power supply must be within this range and well regulated. The current capability of upper power should not exceed the maximum current limit of the power switch.

9.1 Power Supply Decoupling Capacitor

The TPA6211A1-Q1 device requires adequate power supply decoupling to ensure a high efficiency operation with low total harmonic distortion (THD). Place a low equivalent series resistance (ESR) ceramic capacitor, typically 0.1 µF, as close as possible of the V_{DD} pin. This choice of capacitor and placement helps with higher frequency transients, spikes, or digital hash on the line. TI recommends placing a 2.2-µF to 10-µF capacitor on the V_{DD} supply trace. This larger capacitor acts as a charge reservoir, providing energy faster than the board supply, thus helping to prevent any droop in the supply voltage.

10 Layout

10.1 Layout Guidelines

Place all the external components close to the TPA6211A1-Q1 device. The input resistors need to be close to the device input pins so noise does not couple on the high impedance nodes between the input resistors and the input amplifier of the device. Placing the decoupling capacitors, C_S and C_{BYPASS}, close to the TPA6211A1-Q1 device is important for the efficiency of the amplifier. Any resistance or inductance in the trace between the device and the capacitor can cause a loss in efficiency.

10.2 Layout Example

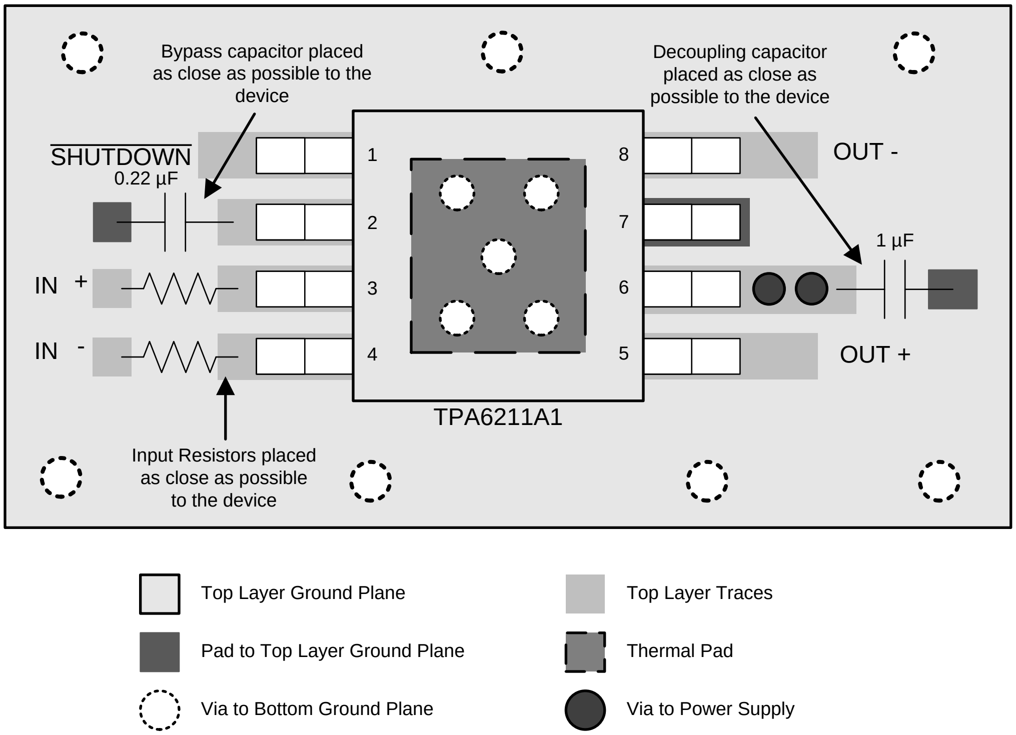


Figure 39. TPA6211A1-Q1 8-Pin MSOP-PowerPAD™ (DGN) Board Layout

11 Device and Documentation Support

11.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.3 Trademarks

PowerPAD, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

11.4 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPA6211A1TDGNRQ1	ACTIVE	MSOP-PowerPAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 105	6211Q	Samples

[1] The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

[3] MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

[4] There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

[5] Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

[6] Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TPA6211A1-Q1 :

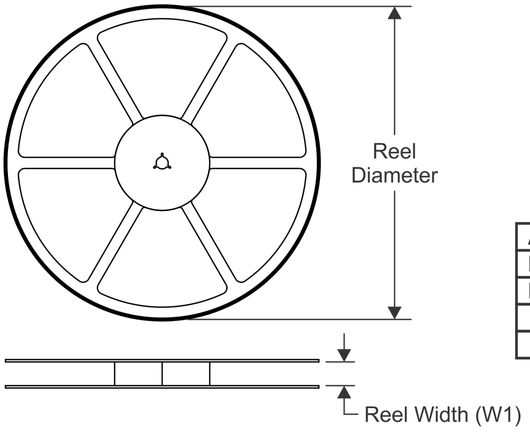
- Catalog: TPA6211A1

NOTE: Qualified Version Definitions:

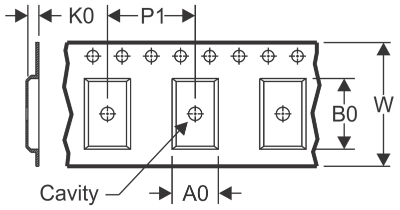
- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

REEL DIMENSIONS

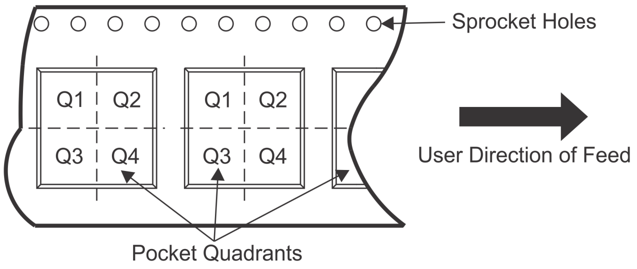


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

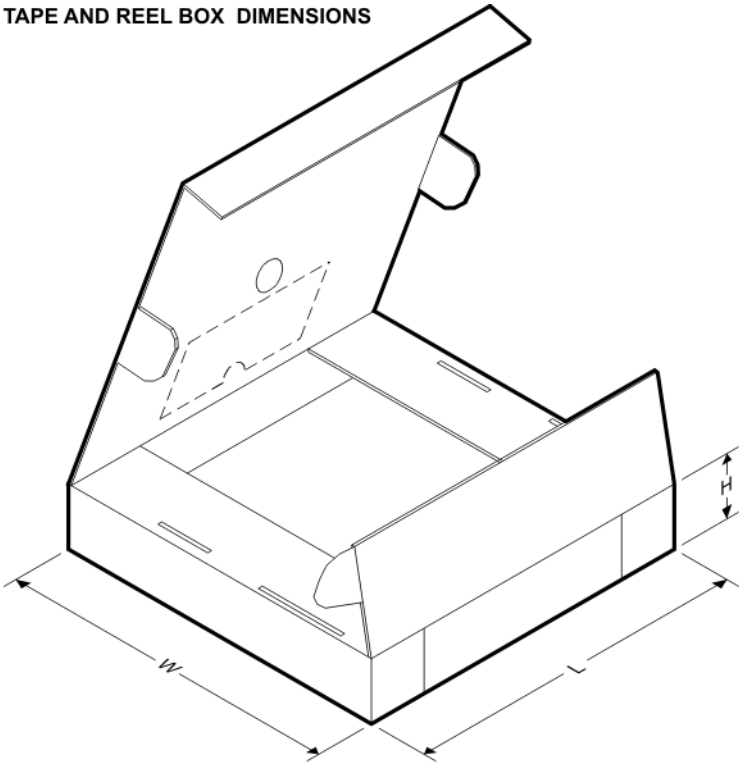
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPA6211A1TDGNRQ1	MSOP-Power PAD	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

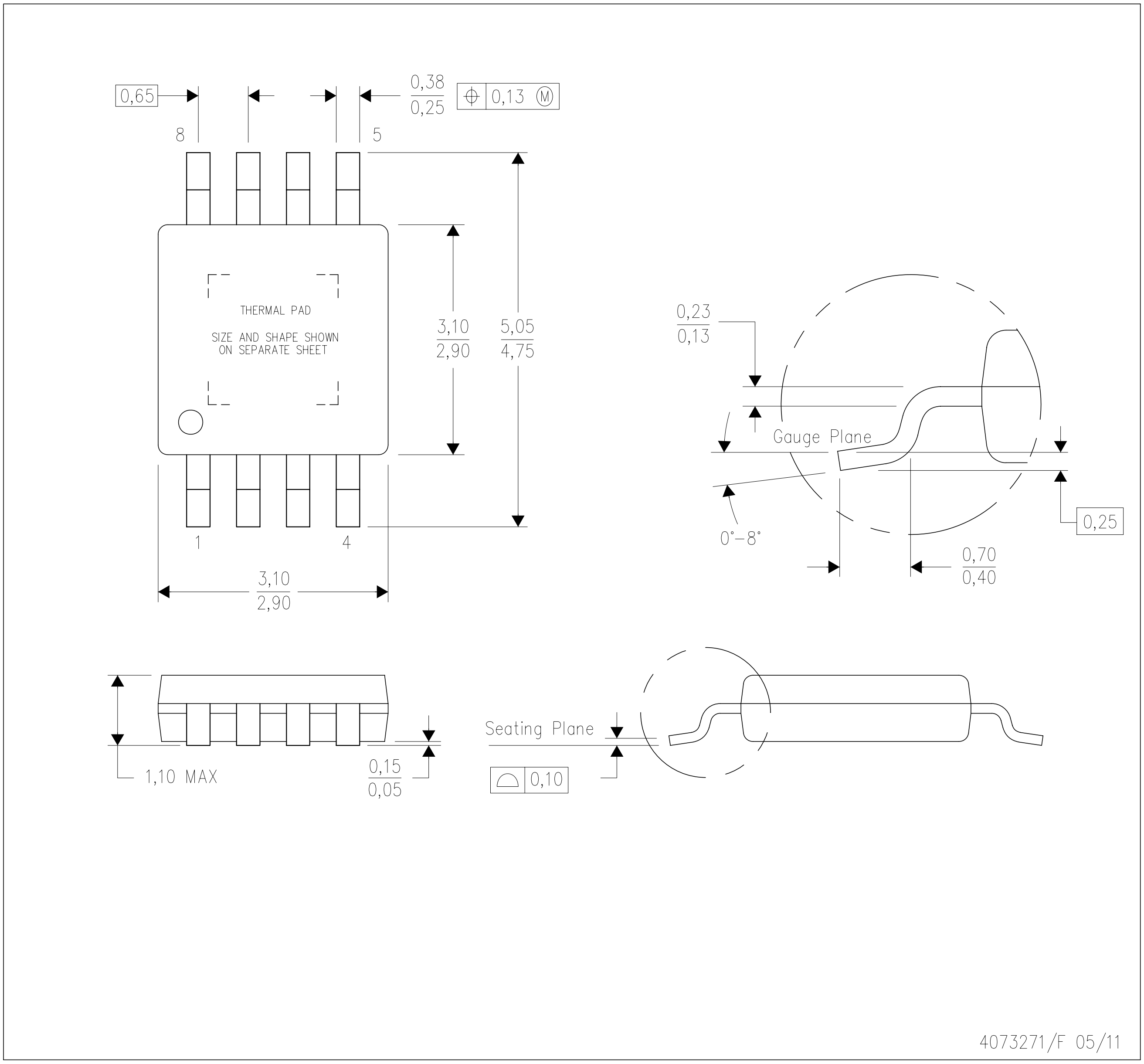
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPA6211A1TDGNRQ1	MSOP-PowerPAD	DGN	8	2500	346.0	346.0	29.0

DGN (S-PDSO-G8) PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <http: //www.ti.com>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO–187 variation AA–T

PowerPAD is a trademark of Texas Instruments.

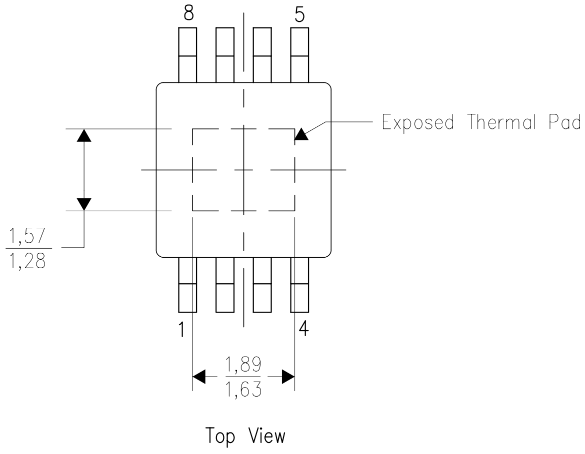
DGN (S–PDSO–G8) PowerPAD™ PLASTIC SMALL OUTLINE

THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

4206323–2/I 12/11

NOTE: All linear dimensions are in millimeters

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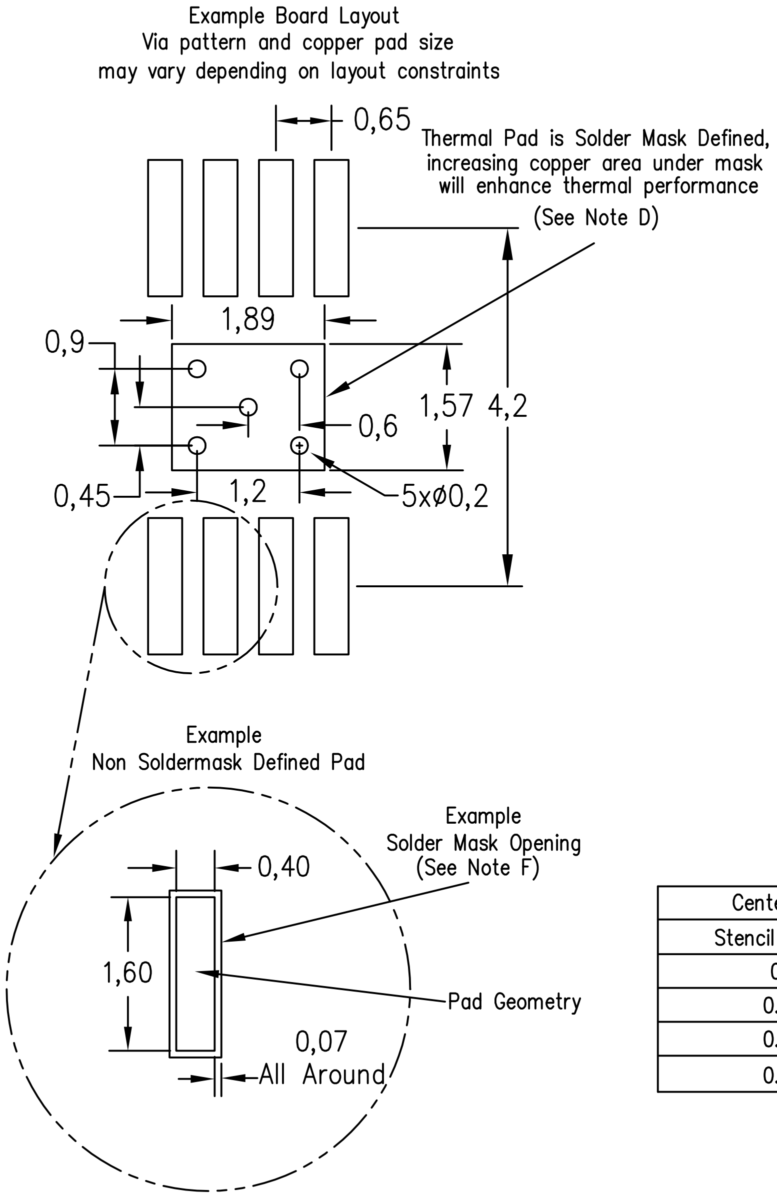
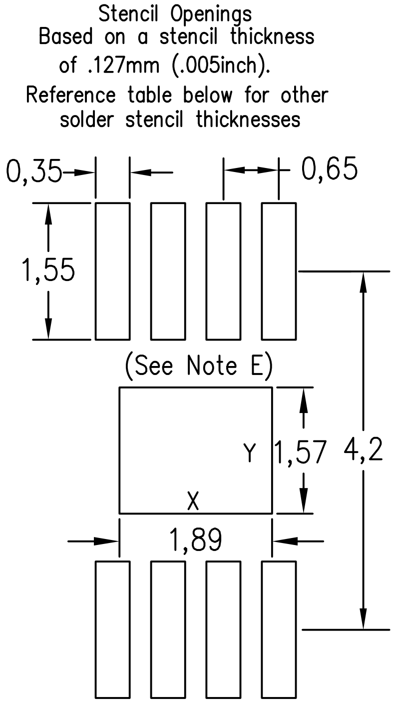
DGN (R–PDSO–G8) PowerPAD™ PLASTIC SMALL OUTLINE





Center Power Pad Solder Stencil Opening		
Stencil Thickness	X	Y
0.1mm	2.0	1.7
0.127mm	1.89	1.57
0.152mm	1.75	1.45
0.178mm	1.65	1.35

4207737–2/F 02/13

NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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